

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE (Rev. 2-32) PATENT AND TRADEMARK OFFICE Information Disclosure Statement by Applicant (Use several sheets if necessary)	ATTY. DOCKET NO. SAR 14108	SERIAL NO To Be Assigned
	APPLICANT John Robertson Tower et al.	
	FILING DATE Herewith	GROUP

U.S. PTO
09/942835
08/30/01

U.S. PATENT DOCUMENTS

Exmr Initial	Document Number	Date	Name	Class	Sub Class	Filing Date
<i>sa</i>	4,608,606	08/26/86	Levine			
<i>sa</i>	5,981,932	11/09/99	Guerrieri et al.			
<i>sa</i>	3,953,733	04/27/76	Levine			
<i>sa</i>	5,151,380	09/29/92	Hynecek			
<i>sa</i>	5,453,632	09/26/95	Hynecek et al.			
<i>sa</i>	4,668,971	05/26/87	Hynecek			
<i>sa</i>	4,229,752	10/21/80	Hynecek			
<i>sa</i>	5,841,159	11/24/98	Lee et al.			
<i>sa</i>	5,881,184	03/09/99	Guidash			
<i>sa</i>	6,069,376	05/30/00	Merrill			
<i>sa</i>	6,141,050	10/31/00	Ackland et al.			
<i>sa</i>	5,591,996	01/07/97	Haigh et al.			
<i>sa</i>	5,742,047	04/21/98	Buhler et al.			
<i>sa</i>	5,808,329	09/15/98	Jack et al.			

FOREIGN PATENT DOCUMENTS

Exmr Initial	Document Number	Date	Country	Class	Sub Class	Translation YES NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

<i>sa</i>	1)	W. F. Keenan et al.; "A Channel-Stop-Defined Barrier and Drain Antiblooming Structure for Virtual Phase CCD Image Sensors"; IEEE Transactions on Electron Devices, vol. 36, no. 9, September 1989.
<i>sa</i>	2)	Y. Matsunaga et al.; "A Highly Sensitive On-Chip Charge Detector for CCD Area Image Sensor"; IEEE Journal of Solid-State Circuits, vol. 26, no. 4, April 1991.
<i>sa</i>	3)	S. Ohsawa et al.; "Analysis of Low Signal Level Characteristics for High-Sensitivity CCD Charge Detector"; IEEE Transactions on Electron Devices, vol. 39, no. 6, June 1992.
<i>sa</i>	4)	Y. Matsunaga et al.; "Ultra High Sensitivity On-Chip Amplifier for VLSI CCD Image Sensor"; ULSI Research Center; 1990 Symposium on VLSI Circuits
<i>sa</i>	5)	E. Roks et al.; "The Double-Sided Floating-Surface Detector: An Enhanced Charge-Detection Architecture For CCD Image Sensors"; IEEE Transactions on Electron Devices, vol. 43, no. 9, September 1996.
<i>sa</i>	6)	B. C. Burkey et al.; "The Pinned Photodiode for an Interline-Transfer CCD Image Sensor"; Research Laboratories, Eastman Kodak Company; December 1984; pgs. 28-31.
<i>sa</i>	7)	E. Meisenzahl et al.; "Charge-Coupled Device Image Sensors"; January 1998; http://www.sensormag.com/articles/0198/cc0198/main.shtml
<i>sa</i>	8)	"An Introduction to Scientific Imaging Charge-Coupled Devices, SiTe CCD Technology for Superior Performance"; Scientific Imaging Technologies, Inc.; 1994.

Examiner <i>Samuel Adams</i>	Date Considered <i>12/27/02</i>
------------------------------	---------------------------------

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.